Analog Power AM20N10-130D MOSFET Datasheet

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Key Features:
Low rDS(on) trench technology
Low thermal impedance
Fast switching speed
Typical Applications:
White LED boost converters
Automotive Systems
Industrial DC/DC Conversion Circuits

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N-Channel 100-V (D-S) MOSFET

Key Features:

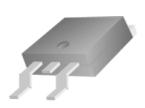
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

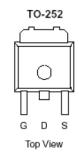
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
100	130 @ V _{GS} = 10V	17		
	160 @ V _{GS} = 4.5V	15		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V_{DS}	100	V		
Gate-Source Voltage		V_{GS}	±20	V		
Continuous Drain Current a	T _A =25°C	I _D	17	Α		
Pulsed Drain Current ^b		I _{DM}	70	^		
Continuous Source Current (Diode Conduction) ^a			42	Α		
Power Dissipation ^a	T _A =25°C	P_{D}	50	W		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

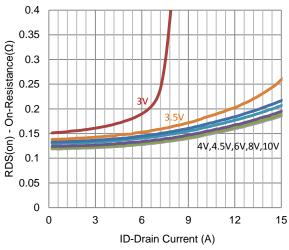
Parameter	Symbol	Symbol Test Conditions		Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$				V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zara Cata Valta da Duaia Cumunt	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25 u/	
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 8.5 \text{ A}$			130	mΩ
Dialii-Source Oil-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$			160	11177
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_D = 8.5 \text{ A}$		15		S
Diode Forward Voltage	V_{SD}	I _S = 21 A, V _{GS} = 0 V		1.03		V
		Dynamic				
Total Gate Charge	Q_g	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V},$		4.9		nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 8.5 \text{ A}$		1.9		
Gate-Drain Charge	Q_gd	ID = 0.5 A		2.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 50 \text{ V}, R_{L} = 3.7 \Omega,$		4		
Rise Time	t _r	$V_{DS} = 50 \text{ V}, K_L = 5.7 \Omega,$ $I_D = 8.5 \text{ A},$		6		ne
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		19		ns
Fall Time	t _f	v _{GEN} = 10 v, r(_{GEN} = 0.22		7		
Input Capacitance	C_{iss}			398		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		43		pF
Reverse Transfer Capacitance	C_{rss}			34		

Notes

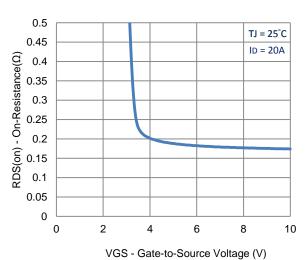
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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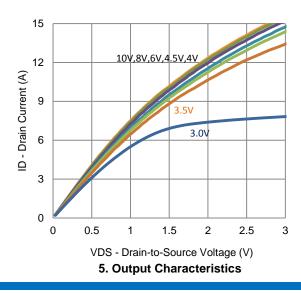
Typical Electrical Characteristics

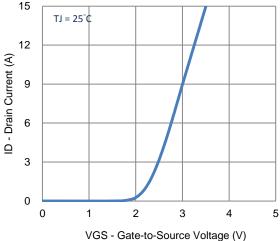


1. On-Resistance vs. Drain Current

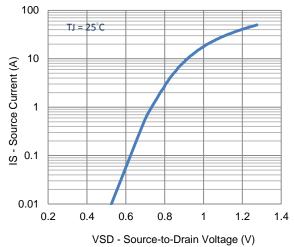


3. On-Resistance vs. Gate-to-Source Voltage

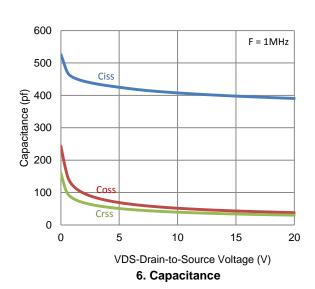




2. Transfer Characteristics



4. Drain-to-Source Forward Voltage

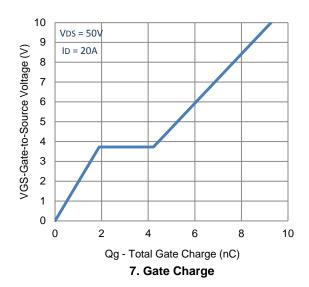


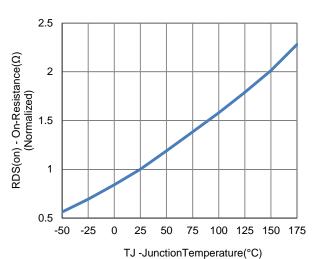
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Publication Order Number: DS_AM20N10-130D_1A

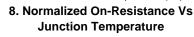
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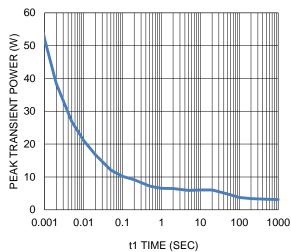
Typical Electrical Characteristics





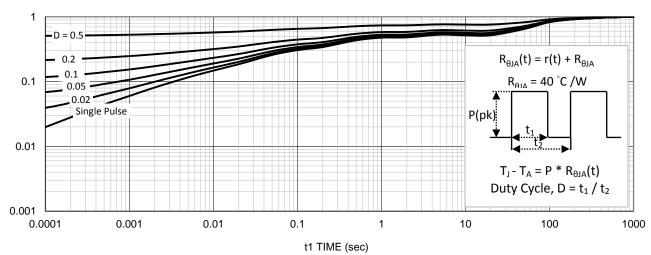
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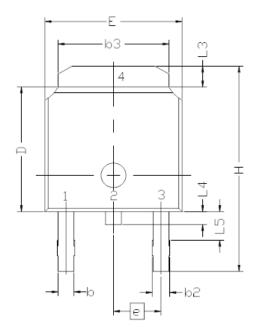
VDS Drain to Source Voltage (V)
9. Safe Operating Area

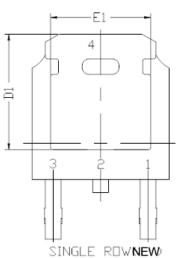
10. Single Pulse Maximum Power Dissipation

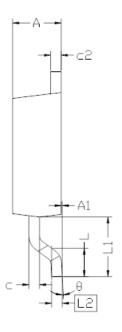


11. Normalized Thermal Transient Junction to Ambient

Package Information







CVADEL	DIMENS:		REQMTS			
SYMBOL	MIN	NDM	MAX			
E	6.40	6.60	6.731			
L	1.40	1.52	1.77			
_L1		2.743 REF				
		.508 BS				
L3	0.89		1.27			
L4	0.64		1.01			
L5						
D	6.00	6.10	6,223			
Н	9.40	10.00	10.40			
b	0.64	0.76	0.88			
b2	0.77	0.84	1.14			
b3	5.21	5.34	5,46			
е		286 BS				
Ā	2,20	2,30	2,38			
A1	0		0.127			
C	0.45	0.50	0.60			
c2	0.45	0.50	0,58			
D1	5,30					
E1	4.40					
θ	0°		10°			

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.